**INVESTIGATION OF silicon photomultipliers AFTER IRRADIATION WITH NEUTRONS UP TO 2×1013 N/CM²**

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Results on the radiation hardness of SiPMs to fast neutrons are presented. SiPMs from Hamamatsu and FBK were irradiated with reactor neutrons up to 1 MeV equivalent fluence of 2\*1013 n/cm2 . The effects of this radiation on many parameters such as gain, intrinsic dark current, photon detection efficiency and noise for these devices are shown and discussed.